■ #12 / 10-26-01 Andt-A

520.37546X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:

TORII et al.

Serial No.:

09/391,250

Filed:

September 7, 1999

For:

SEMICONDUCTOR DEVICE AND ITS FABRICATION

METHOD

Group:

2811

Examiner:

C. Nguyen

AMENDMENT

Assistant Commissioner for Patents Washington, D.C. 20231 October 22, 2001

Sir:

In response to the Office Action dated June 20, 2001, the period of response for which extension is requested by the attached Petition for Extension of Time, please amend the above-identified application as follows:

In the Title:

Please amend the title to read:

"Memory Structure With A Ferroelectric Capacitor And A Fabrication Method Thereof"